

K Lakshmi Ganapathi

List of Publications by Year in descending order

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611
citing authors

#	ARTICLE	IF	CITATIONS
1	Development of titanium nitride thin film microheaters using laser micromachining. Vacuum, 2022, 197, 110795.	1.6	11
2	Diamondâ€™the ultimate material for exploring physics of spin-defects for quantum technologies and diamondtronics. Journal Physics D: Applied Physics, 2022, 55, 333002.	1.3	4
3	Thickness-Dependent Nonlinear Electrical Conductivity of Few-Layer Muscovite Mica. Physical Review Applied, 2022, 17, .	1.5	5
4	A review on realizing the modern optoelectronic applications through persistent photoconductivity. Journal Physics D: Applied Physics, 2022, 55, 393001.	1.3	11
5	Performance tunability of field-effect transistors using MoS ₂ (1âˆ’x)Se _{2x} alloys. Nanotechnology, 2021, 32, 435202.	1.3	1
6	Development of CeO ₂ -HfO ₂ Mixed Oxide Thin Films for High Performance Oxygen Sensors. IEEE Sensors Journal, 2021, 21, 18326-18333.	2.4	6
7	Optimization and integration of ultrathin e-beam grown HfO ₂ gate dielectrics in MoS ₂ transistors. Journal Physics D: Applied Physics, 2021, 54, 445302.	1.3	4
8	Intercalated water mediated electromechanical response of graphene oxide films on flexible substrates. Journal of Physics Condensed Matter, 2021, 34, .	0.7	0
9	Ultra-Wide Bandgap Copper Oxide: High Performance Solar-Blind Photo-detection. IEEE Electron Device Letters, 2020, 41, 1790-1793.	2.2	12
10	Novel fabrication technique for NiTi and TiN micro-structures by femtosecond lasers. IOP Conference Series: Materials Science and Engineering, 2020, 872, 012113.	0.3	0
11	Long-Lasting Persistent Photoconductivity in Au/CuO Thin Films for Optical Memory. IEEE Photonics Technology Letters, 2020, 32, 329-332.	1.3	9
12	Nanoscale Probing of Magnetic and Electrical Properties of YIG/Si (100) Thin Films Grown by Pulsed Laser Deposition. IEEE Magnetics Letters, 2020, 11, 1-5.	0.6	1
13	Stacking angle dependent multiple excitonic resonances in bilayer tungsten diselenide. Nanophotonics, 2020, 9, 3881-3887.	2.9	3
14	Plasmon-Assisted Selective Enhancement of Direct-Band Transitions in Multi-Layer MoS ₂ . IEEE Photonics Journal, 2019, 11, 1-6.	1.0	2
15	RF Sputtered CeO ₂ Thin Films-Based Oxygen Sensors. IEEE Sensors Journal, 2019, 19, 10821-10828.	2.4	20
16	Probing defect states in few-layer MoS_2 by conductance fluctuation spectroscopy. Physical Review B, 2019, 99, .	1.1	1
17	Exciton Lasing in ZnO-ZnCr ₂ O ₄ Nanowalls. IEEE Photonics Journal, 2019, 11, 1-7.	1.0	2
18	Adaptive Transport in High Performance (I on), Steep Sub-Threshold Slope (SS < 60 mV/dec) MoS ₂ Transistors. IEEE Nanotechnology Magazine, 2019, 18, 1071-1078.	1.1	2

#	ARTICLE	IF	CITATIONS
19	ZnO/Au/ZnO Configuration for High Performance Multiband UV Photo-Detection. , 2019, 3, 1-4.		4
20	Plasmon induced brightening of dark exciton in monolayer WSe ₂ for quantum optoelectronics. Applied Physics Letters, 2019, 114, 201101.	1.5	12
21	High-Performance Broadband Photo-Detection in Solution-Processed ZnO-ZnCr ₂ O ₄ Nanowalls. IEEE Electron Device Letters, 2019, 40, 1143-1146.	2.2	11
22	Hole Injection and Rectifying Heterojunction Photodiodes through Vacancy Engineering in MoS ₂ . Advanced Electronic Materials, 2019, 5, 1800863.	2.6	7
23	Polarization induced switching in PZT back gated multilayer MoS ₂ FETs for low power non-volatile memory. Semiconductor Science and Technology, 2019, 34, 055016.	1.0	6
24	Dielectric based charge carrier tuning for CNT CMOS inverters. Semiconductor Science and Technology, 2019, 34, 015015.	1.0	2
25	Solution-Processed Transparent CuO Thin Films for Solar-Blind Photodetection. IEEE Electron Device Letters, 2019, 40, 255-258.	2.2	19
26	Interface states reduction in atomic layer deposited TiN/ZrO ₂ /Al ₂ O ₃ /Ge gate stacks. Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics, 2018, 36, 021201.	0.6	1
27	Pulsed DC magnetron sputtered titanium nitride thin films for localized heating applications in MEMS devices. Sensors and Actuators A: Physical, 2018, 272, 199-205.	2.0	22
28	Near Infrared Random Lasing in Multilayer MoS ₂ . ACS Omega, 2018, 3, 14097-14102.	1.6	13
29	Dielectric Engineering of HfO ₂ Gate-Stacks for Normally-ON GaN HEMTs on 200-mm Silicon Substrates. IEEE Transactions on Electron Devices, 2018, 65, 3711-3718.	1.6	10
30	Nitride Dielectric Environments to Suppress Surface Optical Phonon Dominated Scattering in High-Performance Multilayer MoS ₂ FETs. Advanced Electronic Materials, 2017, 3, 1600358.	2.6	20
31	(Invited) Interface Engineering of High-k Dielectrics and Metal Contacts for High Performance Top-Gated MoS ₂ FETs. ECS Transactions, 2017, 80, 101-107.	0.3	3
32	A sub-thermionic MoS ₂ FET with tunable transport. Applied Physics Letters, 2017, 111, .	1.5	32
33	Electrical, optical, structural and chemical properties of Al ₂ TiO ₅ films for high- ϵ° gate dielectric applications. Materials Science in Semiconductor Processing, 2017, 57, 137-146.	1.9	7
34	Realizing P-FETs and photodiodes on MoS ₂ through area-selective p-doping via vacancy engineering. , 2017, , .		0
35	Reduction of interface states in Ge/High-k gate stacks and its reliability implications. , 2016, , .		0
36	High Performance HfO ₂ Back Gated Multilayer MoS ₂ transistors. IEEE Electron Device Letters, 2016, , 1-1.	2.2	31

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37	Effect of Post Plasma Oxidation on Ge Gate Stacks Interface Formation. ECS Transactions, 2016, 72, 303-312.	0.3	4
38	Surface State Engineering of Metal/MoS ₂ Contacts Using Sulfur Treatment for Reduced Contact Resistance and Variability. IEEE Transactions on Electron Devices, 2016, 63, 2556-2562.	1.6	44
39	Intrinsic Limit for Contact Resistance in Exfoliated Multilayered MoS ₂ FET. IEEE Electron Device Letters, 2016, 37, 119-122.	2.2	18
40	Optical-Phonon-Limited High-Field Transport in Layered Materials. IEEE Transactions on Electron Devices, 2016, 63, 767-772.	1.6	7
41	Influence of O ₂ flow rate on HfO ₂ gate dielectrics for back-gated graphene transistors. Semiconductor Science and Technology, 2014, 29, 055007.	1.0	18
42	Pulsed DC Magnetron Sputtered Rutile TiO ₂ films for next generation DRAM capacitors. Materials Research Society Symposia Proceedings, 2013, 1561, 1.	0.1	0
43	Optimization of HfO ₂ films for high transconductance back gated graphene transistors. Applied Physics Letters, 2013, 103, .	1.5	18